



NTE5826 thru NTE5829 Silicon Power Rectifier Diode, 50 Amp, Press Fit

Description:

The NTE5826 thru NTE5829 are silicon power rectifier diodes in a press-fit type package designed for use in all medium-current applications or for higher current industrial alternators and chassis mounted power supply rectifiers.

Features:

- 50 Amp @ $T_C = +150^\circ\text{C}$
- 600 Amp Surge Capability
- Rugged Construction
- Available in Standard (NTE5826, NTE5828) and Reverse (NTE5827, NTE5829) Polarity

Absolute Maximum Ratings:

Peak Repetitive Reverse Voltage, V_{RRM}

NTE5826, NTE5827*	400V
NTE5828, NTE5829*	800V

Working Peak Reverse Voltage, V_{RWM}

NTE5826, NTE5827*	400V
NTE5828, NTE5829*	800V

DC Blocking Voltage, V_B

NTE5826, NTE5827*	400V
NTE5828, NTE5829*	800V

Non-Repetitive Peak Reverse Voltage, V_{RSM}

NTE5826, NTE5827*	450V
NTE5828, NTE5829*	850V

RMS Reverse Voltage, $V_{R(RMS)}$

NTE5826, NTE5827*	280V
NTE5828, NTE5829*	560V

Average Rectified Forward Current (Single phase, resistive load, $T_C = +150^\circ\text{C}$), I_O 50A

Non-Repetitive Peak Surge Current (Surge applied at rated load conditions), I_{FSM} 600A

Operating Junction Temperature Range, T_J -65° to $+195^\circ\text{C}$

Storage Temperature Range, T_{stg} -65° to $+195^\circ\text{C}$

Maximum Thermal Resistance, Junction-to-Case, R_{thJC} 0.8°C/W

Note 1. Standard polarity is cathode to case, (*) indicated anode to case.

Electrical Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Instantaneous Forward Voltage	V_F	$I_F = 157\text{A}$, $T_J = +25^\circ\text{C}$	–	1.10	1.18	V
		$I_F = 50\text{A}$, $T_J = +25^\circ\text{C}$	–	0.95	1.00	V
Reverse Current	I_R	$V_{RRM} = \text{Rated Voltage}$, $T_C = +25^\circ\text{C}$	–	0.05	0.2	mA
		$V_{RRM} = \text{Rated Voltage}$, $T_C = +150^\circ\text{C}$	–	1.0	2.0	mA

